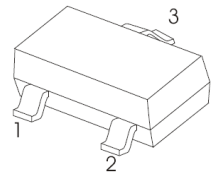
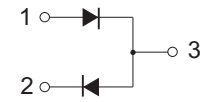
WITCHING DIODE

SOT-23

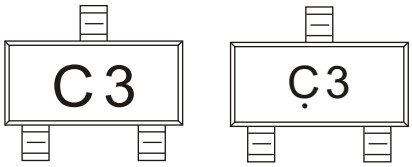




FEATURES

- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

MARKING: C3



Solid dot = Green molding compound device,if none,the normal device.

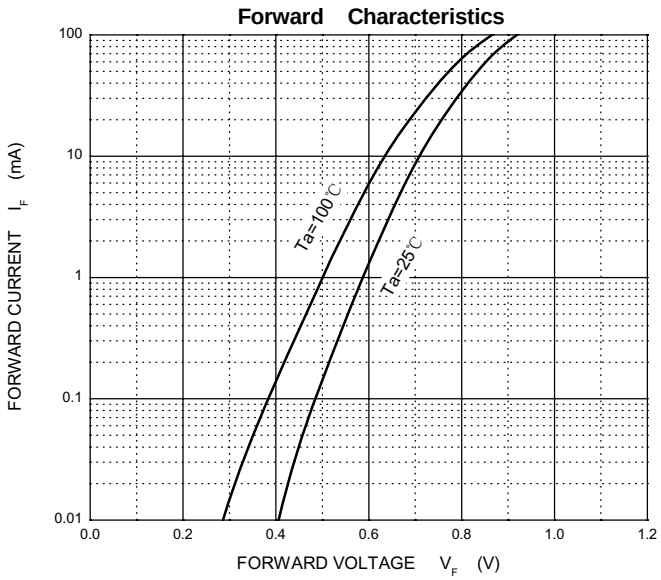
Maximum Ratings ,Single Diode @Ta=25℃

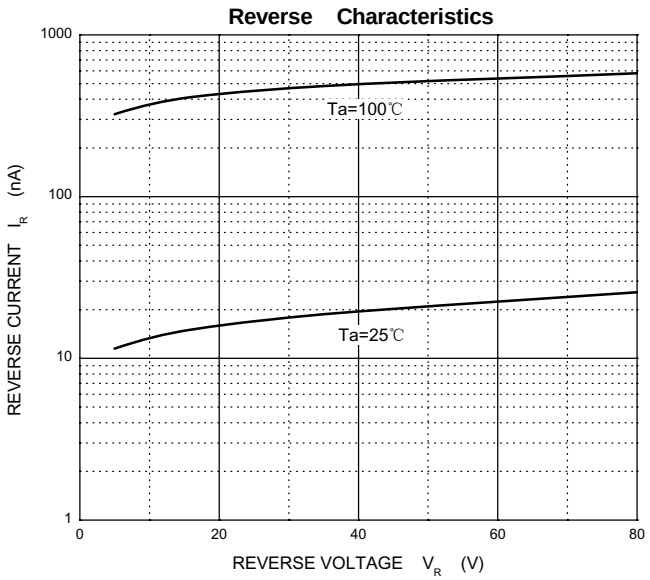
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	85	V
Peak Repetitive Peak Reverse Voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	80	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	100	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2	A
Power Dissipation	P_D	150	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

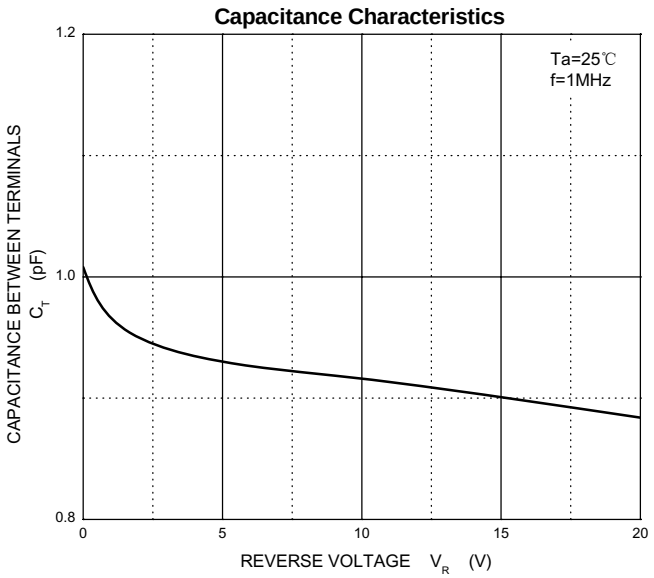
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

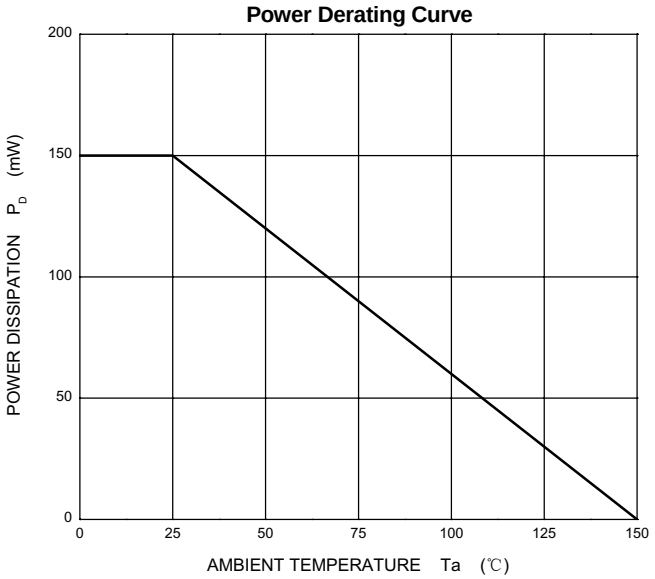
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100uA	80		V
Reverse voltage leakage current	I_R	V_R=80V		0.5	uA
Forward voltage	V_F	I_F=100mA		1.2	V
Diode capacitance	C_D	V_R=0V, f=1MHz		3	pF
Reverse recovery time	t_{rr}	I_F=10mA		4	ns

Typical Characteristics

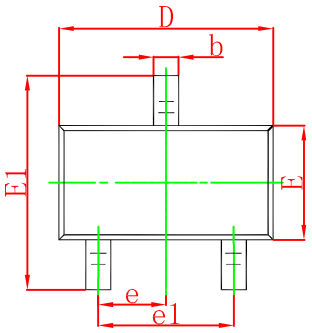


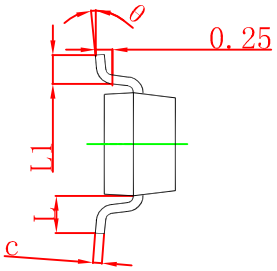


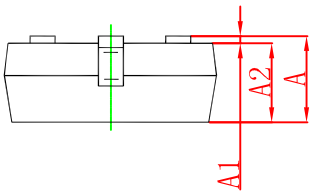




SOT-23 Package Outline Dimensions

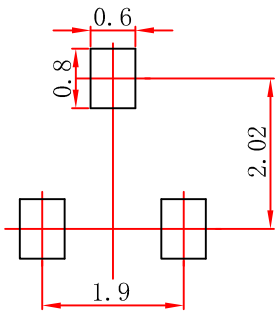






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.